

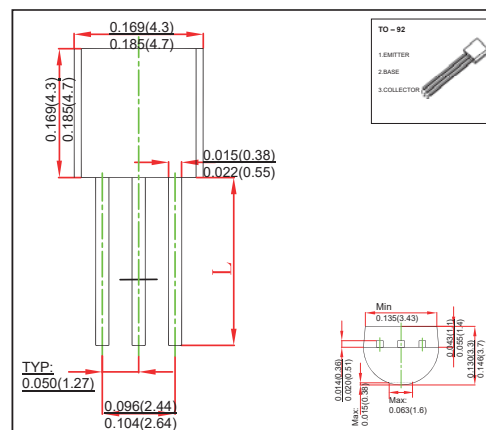
## TO-92 Plastic-Encapsulate Transistors

### FEATURE

- Switching and Amplification in High Voltage Applications such as elephony
- Low Current(max. 600mA)
- High Voltage(max.130v)
- TRANSISTOR (PNP)

### MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

| Parameter                               | Symbol       | Value      | Unit  |
|-----------------------------------------|--------------|------------|-------|
| Collector-Base Voltage                  | <b>VCBO</b>  | -130       | V     |
| Collector-Emitter Voltage               | <b>VCEO</b>  | -120       | V     |
| Emitter-Base Voltage                    | <b>VEBO</b>  | -5         | V     |
| Collector Current -Continuous           | <b>IC</b>    | -0.6       | A     |
| Collector Power Dissipation             | <b>PD</b>    | 625        | mW    |
| Thermal Resistance, junction to Ambient | <b>RK JA</b> | 200        | °C /W |
| Junction Temperature                    | <b>Tj</b>    | 150        | °C    |
| Storage Temperature                     | <b>Tstg</b>  | -55 ~ +150 | °C    |

| Parameter                            | Symbol        | Test conditions                         | Min  | Typ | Max  | Unit    |
|--------------------------------------|---------------|-----------------------------------------|------|-----|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C = -100\mu A, I_E = 0$              | -130 |     |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C = -1mA, I_B = 0$                   | -120 |     |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E = -10\mu A, I_C = 0$               | -5   |     |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB} = -100 V, I_E = 0$              |      |     | -0.1 | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB} = -3 V, I_C = 0$                |      |     | -0.1 | $\mu A$ |
| DC current gain                      | $h_{FE1}$     | $V_{CE} = -5 V, I_C = -1mA$             | 30   |     |      |         |
|                                      | $h_{FE2}$     | $V_{CE} = -5 V, I_C = -10mA$            | 40   |     | 180  |         |
|                                      | $h_{FE3}$     | $V_{CE} = -5 V, I_C = -50mA$            | 40   |     |      |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -10mA, I_B = -1mA$               |      |     | -0.2 | V       |
|                                      | $V_{CE(sat)}$ | $I_C = -50mA, I_B = -5mA$               |      |     | -0.5 | V       |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C = -10mA, I_B = -1mA$               |      |     | -1   | V       |
|                                      | $V_{BE(sat)}$ | $I_C = -50mA, I_B = -5mA$               |      |     | -1   | V       |
| Transition frequency                 | $f_T$         | $V_{CE} = -10V, I_C = -10mA, f = 30MHz$ | 100  |     |      | MHz     |
| Collector output capacitance         | $C_{ob}$      | $V_{CB} = -10V, I_E = 0, f = 1MHz$      |      |     | 6    | pF      |